

TOSHIBA

2SC4539

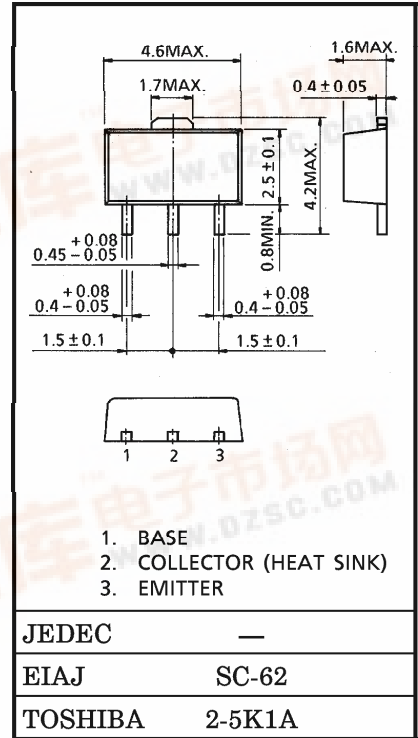
TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL PLANAR TYPE (PCT PROCESS)

2SC4539

POWER AMPLIFIER APPLICATIONS
POWER SWITCHING APPLICATIONS

- Low Saturation Voltage : $V_{CE(sat)} = 0.5V$ (Max.)
($I_C = 700mA$)
- High Speed Switching Time : $t_{stg} = 0.3\mu s$ (Typ.)
- Small Flat Package
- $P_C = 1 \sim 2W$ (Mounted on Ceramic Substrate)
- Complementary to 2SA1734

Unit in mm



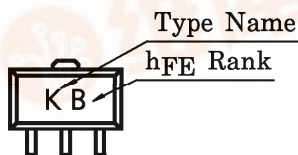
MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	50	V
Collector-Emitter Voltage	V_{CEO}	30	V
Emitter-Base Voltage	V_{EBO}	6	V
Collector Current	I_C	1.2	A
Base Current	I_B	0.3	A
Collector Power Dissipation	P_C	500	mW
Collector Power Dissipation	P_C (Note)	1000	mW
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature Range	T_{stg}	-55~150	$^\circ C$

Weight : 0.05g

(Note) : Mounted on ceramic substrate ($250mm^2 \times 0.4t$)

MARKING



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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I_{CBO}	$V_{CB} = 50V, I_E = 0$	—	—	0.1	μA
Emitter Cut-off Current		I_{EBO}	$V_{EB} = 6V, I_C = 0$	—	—	0.1	μA
Collector-Emitter Breakdown Voltage		$V_{(BR)CEO}$	$I_C = 10mA, I_B = 0$	30	—	—	V
DC Current Gain		$h_{FE(1)}$	$V_{CE} = 2V, I_C = 100mA$	120	—	400	
		$h_{FE(2)}$	$V_{CE} = 2V, I_C = 1.0A$	40	—	—	
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	$I_C = 700mA, I_B = 35mA$	—	—	0.5	V
Base-Emitter Saturation Voltage		$V_{BE(sat)}$	$I_C = 700mA, I_B = 35mA$	—	—	1.2	V
Transition Frequency		f_T	$V_{CE} = 2V, I_C = 100mA$	—	100	—	MHz
Collector Output Capacitance		C_{ob}	$V_{CB} = 10V, I_E = 0, f = 1MHz$	—	10	—	pF
Switching Time	Turn-on Time	t_{on}	<p style="text-align: center;"> $I_{B1} = -I_{B2} = 35mA,$ $DUTY\ CYCLE \leq 1\%$ </p>	—	0.1	—	μs
	Storage Time	t_{stg}		—	0.3	—	
	Fall Time	t_f		—	0.1	—	

